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73. (New)

A substrate processing apparatus comprising:
a processing chamber; and
a gas injection assembly for injecting at least one gas into said processing chamber and being adapted to make the gas injected into said processing chamber into a gas plasma, wherein said gas injection assembly includes a plasma generator and a supply tube, and said plasma generator includes a generator tube in communication with said supply tube and generates an electromagnetic field in said generator tube to make the gas in said supply tube into a gas plasma.

74. (New)

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Cont
A substrate processing apparatus according to Claim 73, wherein said supply tube has a larger diameter than said generator tube such that the gas is made into the gas plasma within said supply tube.

75. (New)

A manufacturing method for a semiconductor device, said method comprising:
processing a semiconductor substrate using a substrate processing apparatus including:

a processing chamber, and
a gas injection assembly for injecting at least one gas into said processing chamber and being adapted to make the gas injected into said processing chamber into a gas plasma, wherein said gas injection assembly includes at least two gas injection tubes, a first of said gas injection tubes injecting a first gas in said processing chamber, a second of said gas injection tubes injecting a second gas in said processing chamber, and said